

Sample &

Buy









### CSD18502Q5B

SLPS320A - NOVEMBER 2012 - REVISED JULY 2015

# CSD18502Q5B 40 V N-Channel NexFET™ Power MOSFET

Technical

Documents

#### Features 1

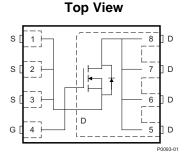
- Ultra-Low Q<sub>a</sub> and Q<sub>ad</sub>
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- **Pb-Free Terminal Plating**
- **RoHS** Compliant
- Halogen-Free
- SON 5 mm × 6 mm Plastic Package

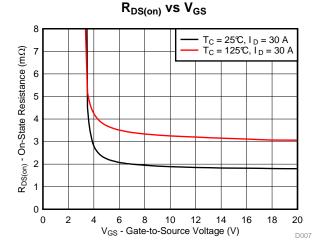
#### Applications 2

- **DC-DC** Conversion
- Secondary Side Synchronous Rectifier
- Motor Control

### 3 Description

This 40-V, 1.8-mΩ, 5 mm × 6 mm NexFET<sup>™</sup> power MOSFET is designed to minimize losses in power conversion applications.





### **Product Summary**

T <sub>A</sub> = 25°	С	TYPICAL VA	UNIT	
V <sub>DS</sub>	Drain to source voltage 40			
Qg	Gate charge total (4.5 V)	25		nC
Q <sub>gd</sub>	Gate charge gate to drain	8.4	nC	
D	Drain to source on resistance	V <sub>GS</sub> = 4.5 V 2.5		mΩ
R <sub>DS(on)</sub>	Drain to source on resistance	V <sub>GS</sub> = 10 V	1.8	mΩ
V <sub>GS(th)</sub>	Threshold voltage	1.8	V	

### Ordering Information<sup>(1)</sup>

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18502Q5B	2500	13-Inch Reel	SON 5 mm × 6 mm	Tape and
CSD18502Q5BT	250	7-Inch Reel	Plastic Package	Reel

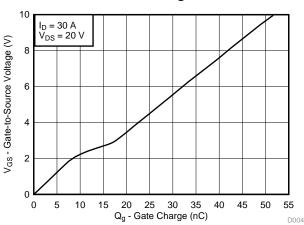
(1) For all available packages, see the orderable addendum at the end of the datasheet.

### **Absolute Maximum Ratings**

T <sub>A</sub> = 2	5°C	VALUE	UNIT
$V_{\text{DS}}$	Drain to source voltage	40	V
$V_{GS}$	Gate to source voltage	±20	V
	Continuous drain current (package limited)	100	
I <sub>D</sub>	Continuous drain current (silicon limited), $T_C = 25^{\circ}C$	204	А
	Continuous drain current <sup>(1)</sup>	26	
I <sub>DM</sub>	Pulsed drain current <sup>(2)</sup>	400	А
P	Power dissipation <sup>(1)</sup>	3.2	W
PD	Power dissipation, $T_C = 25^{\circ}C$	156	vv
TJ	Operating junction temperature	-55 to 150	°C
T <sub>stg</sub>	Storage temperature	-55 to 150	°C
E <sub>AS</sub>	Avalanche energy, single pulse $I_{D}$ = 88 A, L = 0.1 mH, $R_{G}$ = 25 $\Omega$	387	mJ

(1) Typical  $R_{\theta JA}$  = 40°C/W on a 1 inch² , 2 oz. Cu pad on a 0.06 inch thick FR4 PCB.

(2) Max  $R_{\theta JC} = 0.8^{\circ}C/W$ , pulse duration  $\leq 100 \ \mu s$ , duty cycle  $\leq 1\%$ 



### **Gate Charge**

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



2

## Table of Contents

1 Features ..... 1 2 Applications ..... 1 3 Description ..... 1 4 Revision History...... 2 5 5.2 Thermal Information ...... 3 5.3 Typical MOSFET Characteristics ...... 4 Device and Documentation Support......7 6

# 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

### Changes from Original (November 2012) to Revision A

### 

6.1 6.2 Trademarks ...... 7 Electrostatic Discharge Caution ...... 7 6.3 Glossary.....7 6.4 7 Mechanical, Packaging, and Orderable Information ...... 8 Q5B Package Dimensions ...... 8 7.1 72 7.3 Q5B Tape and Reel Information ..... 10 7.4

Copyright © 2012-2015, Texas Instruments Incorporated



www.ti.com

#### Page

### **5** Specifications

### 5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS				
$BV_{DSS}$	Drain to source voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	40		V
I <sub>DSS</sub>	Drain to source leakage current	$V_{GS} = 0 V, V_{DS} = 32 V$		1	μA
I <sub>GSS</sub>	Gate to source leakage current	$V_{DS} = 0 V, V_{GS} = 20 V$		100	nA
V <sub>GS(th)</sub>	Gate to source threshold voltage	$V_{DS} = V_{GS}, \ I_D = 250 \ \mu A$	1.5 1.8	2.2	V
C	Drain to course on registeres	$V_{GS} = 4.5 \text{ V}, I_{D} = 30 \text{ A}$	2.5	3.3	mΩ
R <sub>DS(on)</sub>	Drain to source on resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	1.8	2.3	mΩ
g <sub>fs</sub>	Transconductance	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	143		S
DYNAMI	C CHARACTERISTICS				
C <sub>iss</sub>	Input capacitance		3900	5070	pF
C <sub>oss</sub>	Output capacitance	$V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz$	900	1170	pF
C <sub>rss</sub>	Reverse transfer capacitance		21	27	pF
$R_G$	Series gate resistance		1.2	2.4	Ω
Qg	Gate charge total (4.5 V)		25	33	nC
Qg	Gate charge total (10 V)		52	68	nC
Q <sub>gd</sub>	Gate charge gate to drain	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	8.4		nC
Q <sub>gs</sub>	Gate charge gate to source		10.3		nC
Q <sub>g(th)</sub>	Gate charge at V <sub>th</sub>		6.9		nC
Q <sub>oss</sub>	Output charge	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	59		nC
t <sub>d(on)</sub>	Turn on delay time		5.3		ns
t <sub>r</sub>	Rise time	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V,	6.8		ns
t <sub>d(off)</sub>	Turn off delay time	$I_{DS} = 30 \text{ A}, \text{ R}_{G} = 0 \Omega$	23		ns
t <sub>f</sub>	Fall time		4		ns
DIODE C	CHARACTERISTICS				
$V_{SD}$	Diode forward voltage	$I_{SD} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	0.8	1	V
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DS</sub> = 20 V, I <sub>F</sub> = 30 A,	88		nC
t <sub>rr</sub>	Reverse recovery time	di/dt = 300 A/µs	44		ns

### 5.2 Thermal Information

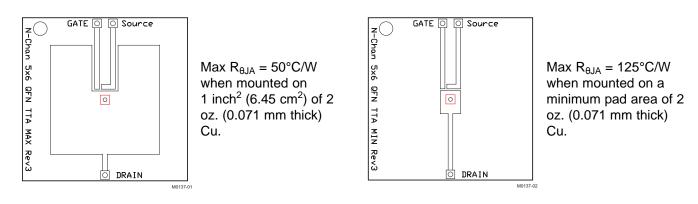
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case (top of package) thermal resistance <sup>(1)</sup>			0.8	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)(2)</sup>			50	°C/W

 $R_{\theta JC}$  is determined with the device mounted on a 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inch x 1.5 inch (3.81 cm x 3.81 cm), 0.06 inch (1.52 mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 material with 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>), 2 oz. (0.071 mm thick) Cu. (1)

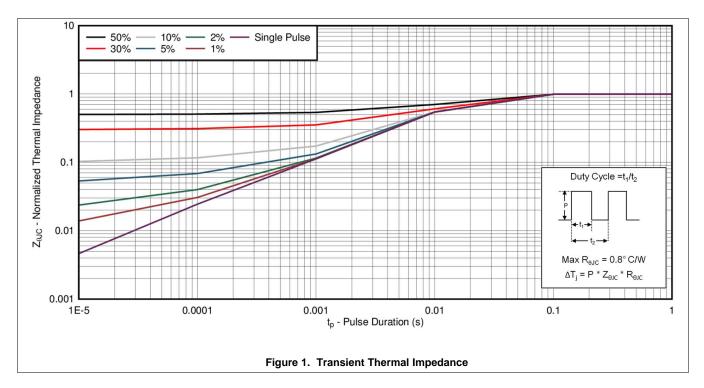
(2)





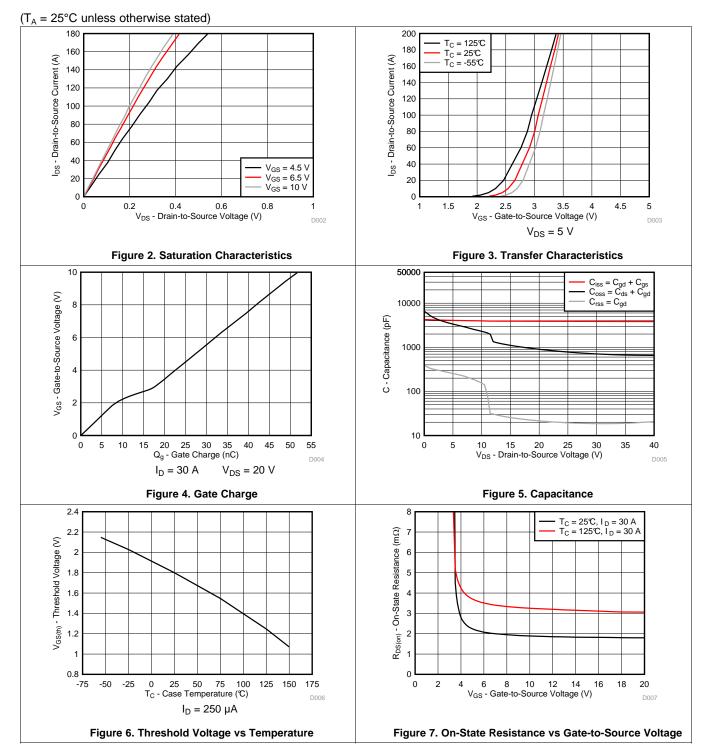
### 5.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 





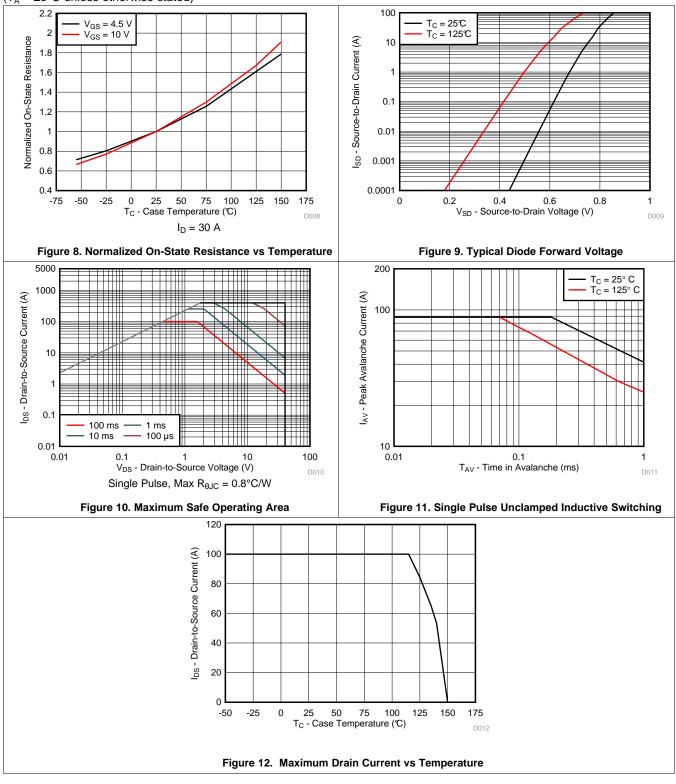
### **Typical MOSFET Characteristics (continued)**





### **Typical MOSFET Characteristics (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 





### 6 Device and Documentation Support

### 6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 6.2 Trademarks

NexFET, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

### 6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 6.4 Glossary

SLYZ022 — TI Glossary.

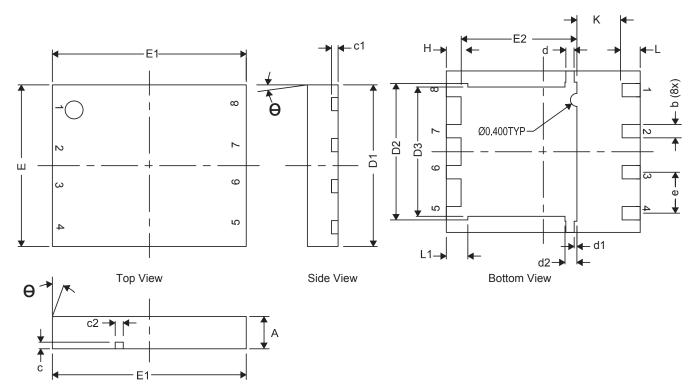
This glossary lists and explains terms, acronyms, and definitions.

CSD18502Q5B SLPS320A – NOVEMBER 2012–REVISED JULY 2015 TEXAS INSTRUMENTS

www.ti.com

## 7 Mechanical, Packaging, and Orderable Information

## 7.1 Q5B Package Dimensions

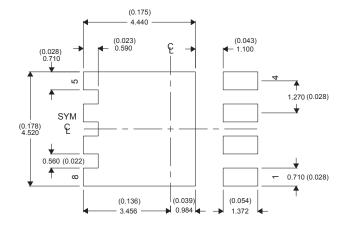


Front View

DIM	MILLIMETERS				
DIM	MIN	NOM	MAX		
А	0.95	1.00	1.05		
b	0.36	0.41	0.46		
С	0.15	0.20	0.25		
c1	0.15	0.20	0.25		
c2	0.20	0.25	0.30		
D1	4.90	5.00	5.10		
D2	4.12	4.22	4.32		
d	0.20	0.25	0.30		
E	4.90	5.00	5.10		
E1	5.90	6.00	6.10		
E2	3.48	3.58	3.68		
е		1.27 TYP			
L	0.46	0.56	0.66		
θ	0°	_	_		
К		1.40 TYP			

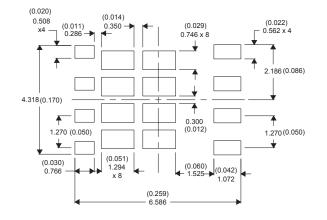


### 7.2 Recommended PCB Pattern

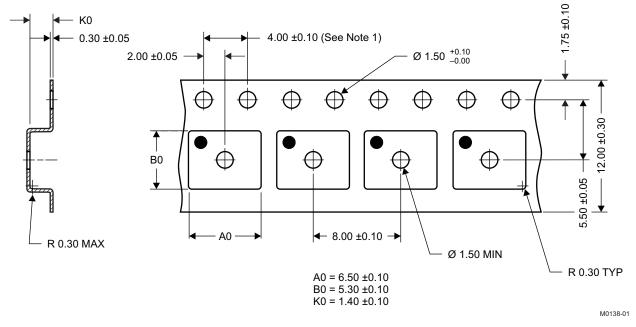


For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

### 7.3 Recommended Stencil Pattern



### 7.4 Q5B Tape and Reel Information



### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket



5-Apr-2016

## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD18502Q5B	ACTIVE	VSON-CLIP	DNK	8	2500	Pb-Free (RoHS Exempt)	CU NIPDAU   CU SN	Level-1-260C-UNLIM		CSD18502	Samples
CSD18502Q5BT	ACTIVE	VSON-CLIP	DNK	8	250	Pb-Free (RoHS Exempt)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18502	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.



5-Apr-2016

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

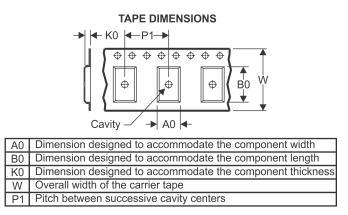
## PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

### TAPE AND REEL INFORMATION





### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18502Q5B	VSON- CLIP	DNK	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1
CSD18502Q5B	VSON- CLIP	DNK	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1
CSD18502Q5BT	VSON- CLIP	DNK	8	250	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1
CSD18502Q5BT	VSON- CLIP	DNK	8	250	178.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

TEXAS INSTRUMENTS

www.ti.com

## PACKAGE MATERIALS INFORMATION

30-Jul-2016



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18502Q5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0
CSD18502Q5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0
CSD18502Q5BT	VSON-CLIP	DNK	8	250	335.0	335.0	32.0
CSD18502Q5BT	VSON-CLIP	DNK	8	250	210.0	210.0	52.0

### **IMPORTANT NOTICE**

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconne	ctivity	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2016, Texas Instruments Incorporated